Supporting Information

Filament theory based WORM memory devices using aluminum/poly (9-vinylcarbazole)/aluminum structures

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Figures

Figure S1. IV characteristic of Al/PVK/Al device with voltage sweeping sequentially from 0 V to - 5 V, -5 V to +5 V and then +5 V to 0 V

Figure S2. (a) Cross sectional (before biasing) and (b) top electrode view (after biasing) SEM images of Al/PVK/Al device

Figure S3 (a)Energy level diagram of the Al/PVK/Al structure and (b) I-V characteristic of the device within the ON region from -1 V to +1 V

Figure S4. Schematic of the filament formation and rupturing resulting in the (a) ON and (b) OFF state respectively

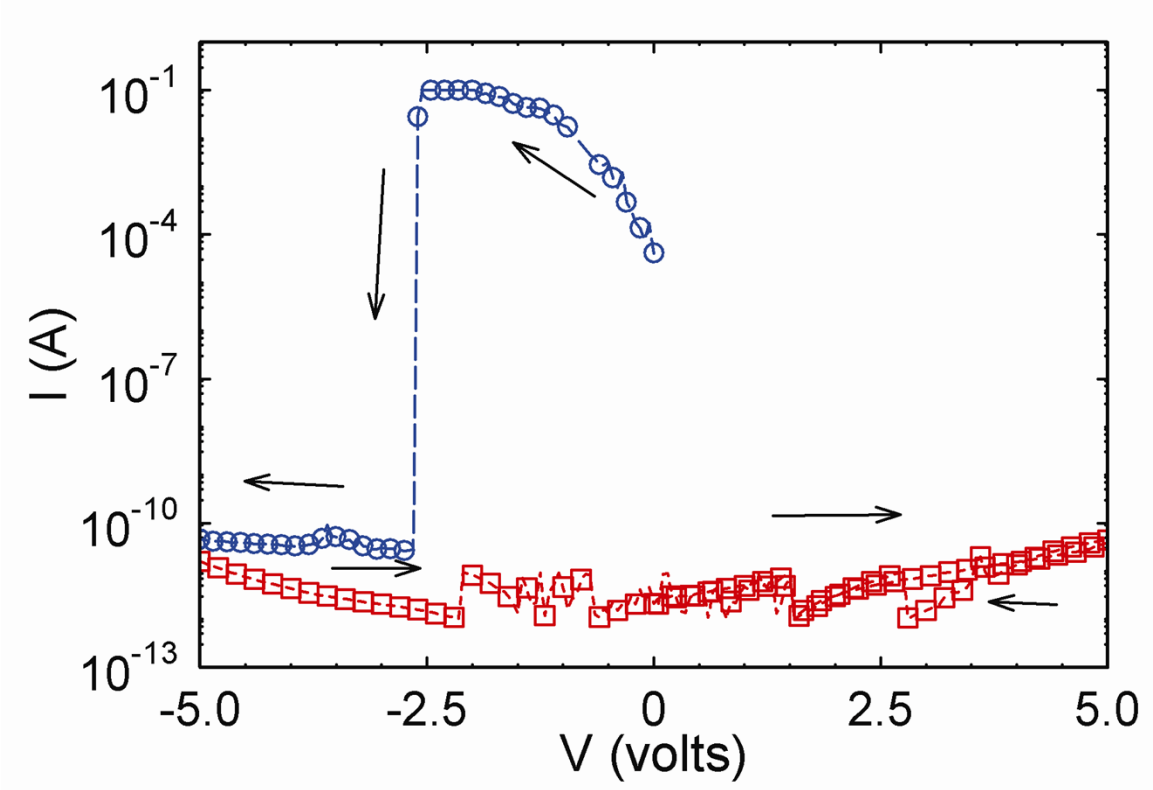
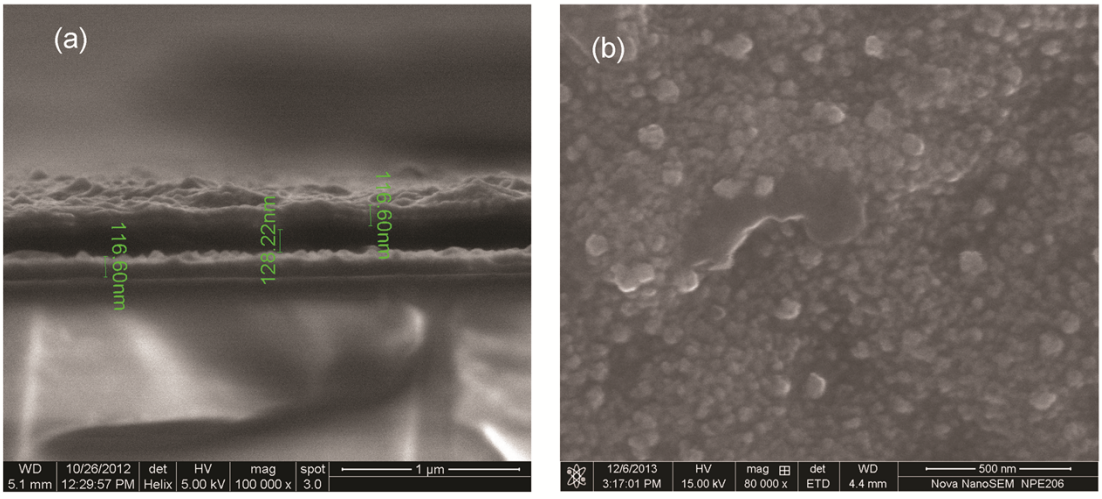


Figure S1. IV characteristic of Al/PVK/Al device with voltage sweeping sequentially from 0 V to -5 V, -5 V to +5 V and then +5 V to 0 V.



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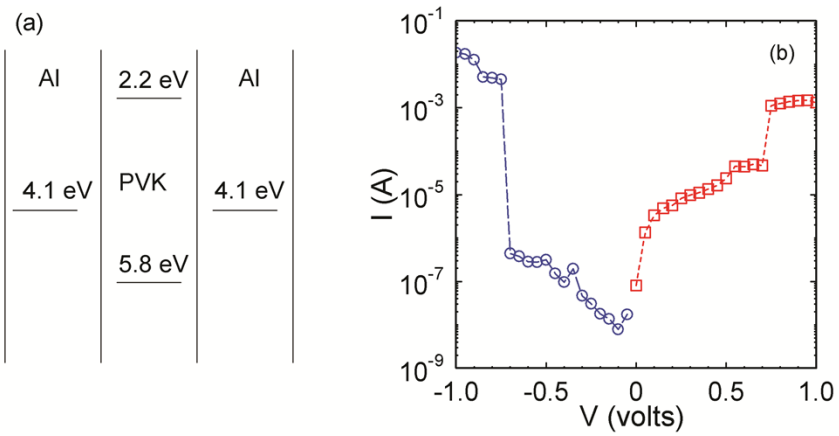
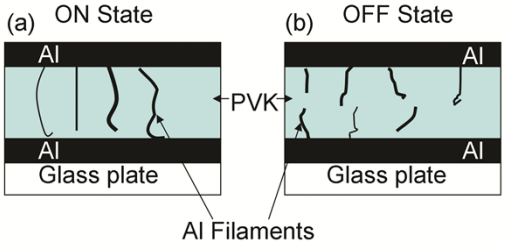


Figure S3 (a) Energy level diagram of the Al/PVK/Al structure and (b) I-V characteristic of the device within the ON region from -1 V to +1 V



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